

LISTING OF THE CLAIMS (1-34)

Claim 1 (currently amended): A process for making a semiconductor structure, comprising:

etching away portions of a conductive layer on a substrate ~~with~~ using a decoupled plasma comprising oxygen and chlorine, wherein said conductive layer is adhered to said substrate by an adhesive layer of at most 500 angstroms in thickness.

Claim 2 (canceled)

Claim 3 (original): The process of claim 1, wherein said conductive layer and said adhesive layer after etching have a combined thickness of at most 3000 angstroms.

Claim 4 (original): The process of claim 1, wherein said adhesive has a thickness of at most about 100 angstroms.

Claim 5 (original): The process of claim 1, wherein said conductive layer and said adhesive layer after etching have a combined thickness of at most 2600 angstroms.

Claim 6 (original): The process of claim 1, wherein said adhesive layer comprises polysilicon, and said conductive layer comprises a material selected from the group consisting of tungsten and tungsten silicide.

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Claim 7 (original): The process of claim 6, wherein said substrate comprises at least one of the group consisting of silicon oxide and silicon nitride.

Claim 8 (cancelled)

Claim 9 (cancelled)

Claim 10 (original): The method of claim 1, wherein said etching is conducted at a pressure of about 2 mTorr to about 4 mTorr.

Claim 11 (cancelled)

Claim 12 (currently amended): The method of claim 11, wherein a source of said chlorine ~~atoms~~ is chlorine gas provided at a flow rate of between about 40 and about 100 sccm, and a source of said oxygen ~~atoms~~ is oxygen gas provided at a flow rate of about 4 to about 12 sccm.

Claim 13 (original): The method of claim 12, wherein said plasma is produced with a plasma flux source power of about 800 watts to about 1500 watts and a plasma bias power of about 50 watts to about 150 watts.

Claim 14 (original): A method of making a semiconductor device, comprising:

making a semiconductor structure by the method of claim 1, and forming a semiconductor device comprising said semiconductor structure.

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Claim 15 (original): The method of claim 14, wherein said semiconductor device is a non-volatile memory.

Claim 16 (original): A method of making an electrical device, comprising:

making a semiconductor device by the method of claim 14, and forming an electrical device comprising said semiconductor device.

Claims 17-20 (withdraw)

Claims 21-26 (cancelled)

Claims 27-34 (withdrawn)